

Shiwei Feng

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1935114/publications.pdf>

Version: 2024-02-01

48
papers

259
citations

933447

10
h-index

996975

15
g-index

48
all docs

48
docs citations

48
times ranked

199
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of Self-Heating on the Drain Current Transient Response in AlGaIn/GaN HEMTs. IEEE Electron Device Letters, 2014, 35, 345-347.	3.9	33
2	A New Differential Amplitude Spectrum for Analyzing the Trapping Effect in GaN HEMTs Based on the Drain Current Transient. IEEE Transactions on Electron Devices, 2017, 64, 1498-1504.	3.0	26
3	Thermal Fatigue Characteristics of Die Attach Materials for Packaged High-Brightness LEDs. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2012, 2, 1346-1350.	2.5	19
4	Effect of substrate thinning on the electronic transport characteristics of AlGaIn/GaN HEMTs. Solid-State Electronics, 2018, 145, 40-45.	1.4	16
5	Effect of poling process on resistive switching in Au/BiFeO ₃ /SrRuO ₃ structures. Applied Physics Letters, 2016, 109, .	3.3	14
6	A current transient method for trap analysis in BiFeO ₃ thin films. Applied Physics Letters, 2018, 112, .	3.3	13
7	A Drain-Source Connection Technique: Thermal Resistance Measurement Method for GaN HEMTs Using TSEP at High Voltage. IEEE Transactions on Electron Devices, 2020, 67, 5454-5459.	3.0	13
8	Effect of Uniaxial Tensile Strains at Different Orientations on the Characteristics of AlGaIn/GaN High-Electron-Mobility Transistors. IEEE Transactions on Electron Devices, 2020, 67, 449-454.	3.0	12
9	Determining Drain Current Characteristics and Channel Temperature Rise in GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2014, 14, 978-982.	2.0	11
10	Determination of Thermal Fatigue Delamination of Die Attach Materials for High-Brightness LEDs. IEEE Photonics Technology Letters, 2012, 24, 398-400.	2.5	10
11	A voltage-transient method for characterizing traps in GaN HEMTs. Microelectronics Reliability, 2019, 93, 57-60.	1.7	10
12	Variation of Dominant Degradation Mechanism in AlGaIn Barrier Layer With Different Voltage Stress on the Gate of AlGaIn/GaN High Electron Mobility Transistors. IEEE Electron Device Letters, 2015, 36, 321-323.	3.9	9
13	Identifying the Properties of Traps in GaN High-Electron-Mobility Transistors via Amplitude Analysis Based on the Voltage-Transient Method. IEEE Transactions on Electron Devices, 2021, 68, 5541-5546.	3.0	7
14	Cycled Thermomechanical Failure in 808-nm High-Power AlGaAs/GaAs Laser Diode Bars. IEEE Transactions on Electron Devices, 2014, 61, 2854-2858.	3.0	6
15	Study of Heat Transport Behavior in GaN-Based Transistors by Schottky Characteristics Method. IEEE Transactions on Electron Devices, 2017, 64, 2166-2171.	3.0	6
16	The study on the thermal behavior of packaged power LEDs. , 2008, , .		5
17	Effects of gamma irradiation on GaN high-electron-mobility transistors characterized by the voltage-transient method. Semiconductor Science and Technology, 2021, 36, 095011.	2.0	5
18	Analysis of junction temperatures in high-power GaN-based LEDs. Science China Technological Sciences, 2010, 53, 297-300.	4.0	4

#	ARTICLE	IF	CITATIONS
19	Evaluation of the Schottky Contact Degradation on the Temperature Transient Measurements in GaN HEMTs. IEEE Transactions on Electron Devices, 2018, 65, 1734-1738.	3.0	4
20	Effects of interfaces and current spreading on the thermal transport of micro-LEDs for kA-per-square-cm current injection levels. RSC Advances, 2019, 9, 24203-24211.	3.6	4
21	A Method of Thermal Analysis for CMOS Integrated Circuit. , 2006, , .		3
22	Transient thermal characteristics related to catastrophic optical damage in high power AlGaAs/GaAs laser diodes. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 2379-2383.	1.8	3
23	A New Method for Measuring Thermal Characteristics of Multistage Depressed Collectors. IEEE Transactions on Electron Devices, 2019, 66, 5404-5406.	3.0	3
24	Analysis of the Effects of High-Energy Electron Irradiation of GaN High-Electron-Mobility Transistors Using the Voltage-Transient Method. IEEE Transactions on Electron Devices, 2021, 68, 3968-3973.	3.0	3
25	Photoresponse of ZnO single crystal films. Frontiers of Optoelectronics in China, 2008, 1, 309-312.	0.2	2
26	Reliability of solder joints in High-power LED package in power cycling tests. , 2010, , .		2
27	Enhanced thermal measurements of high power LEDs by junction characteristic. , 2010, , .		2
28	Thermal stability evaluation of die attach for high brightness LEDs. , 2011, , .		2
29	Structure optimization of heat sink for high power LED street lamp. , 2011, , .		2
30	Effects of Temperature and Bias Voltage on Electron Transport Properties in GaN High-Electron-Mobility Transistors. IEEE Transactions on Device and Materials Reliability, 2021, 21, 494-499.	2.0	2
31	The temperature characteristics of AlGaIn/GaN double heterostructure HEMT's. , 0, , .		1
32	Thermal analysis of ICs based on equivalent thermal resistance. , 2008, , .		1
33	Thermal Analysis of the Multi-Chip Vertical Packaged White LED. , 2009, , .		1
34	Thermal analysis of high power LED array system. , 2010, , .		1
35	Thermal Analysis of GaAs-Based High Power Laser Diodes Related to Degradation. , 2011, , .		1
36	The channel temperature dependence of drain transient response in AlGaIn/GaN HEMTs. , 2014, , .		1

#	ARTICLE	IF	CITATIONS
37	Degradation of the die attach layer in chip-on-board packaged light-emitting diodes during temperature cycling. , 2015, , .		1
38	Characterization of thermal-resistance in Ga ₂ O ₃ Schottky barrier diodes with temperature-sensitive electrical parameters. Semiconductor Science and Technology, 2021, 36, 115010.	2.0	1
39	Thermal analysis of ICS based on equivalent thermal resistance and skill language. , 2009, , .		0
40	The investigation of failure mechanism of n-GaN/Ti/Al/Ni/Au ohmic contact by novel TLM. , 2009, , .		0
41	Thermal resistance analysis related to the degradation of GaAs-Based laser diodes. , 2010, , .		0
42	Reliability evaluation of Schottky contact of AlGaIn/GaN HEMT, based on two AC voltages with different frequencies. , 2010, , .		0
43	Thermal analysis on AlGaInP thin-film LED with ITO p-type contact by electrical method. , 2011, , .		0
44	Quick screen of thermal resistance for batching high brightness LEDs. , 2012, , .		0
45	Transient and long-term catastrophic optical damage in high power AlGaAs/GaAs laser diodes. , 2014, , .		0
46	Thermal analysis of slow-wave structure of helix TWT based on transient temperature rise measurement technology. , 2016, , .		0
47	Temperature distribution and facet coating degradation analysis of 808 nm GaAs-based high-power laser diode bars. , 2017, , .		0
48	Study on 3D thermal transport in micro-LEDs on GaN substrate at the level of kW/cm ² . , 2019, , .		0